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DT12 C'd PCT/PTO 05 JAN 2005

Docket No. 263098US2X PCT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

HB

IN RE APPLICATION OF: Lea DI CIOCCIO, et al.

SERIAL NO: New U.S. PCT Application Based on PCT/FR03/02225

GAU:

FILED: Herewith

EXAMINER:

FOR: METHOD FOR TRANSFERRING AN ELECTRICALLY ACTIVE THIN LAYER

INFORMATION DISCLOSURE STATEMENT UNDER 37 CFR 1.97

COMMISSIONER FOR PATENTS
ALEXANDRIA, VIRGINIA 22313

SIR:

Applicant(s) wish to disclose the following information.

REFERENCES

- The applicant(s) wish to make of record the references cited in the International Search Report and listed on the attached form PTO-1449. Copies of the listed references are attached, where required, as are either statements of relevancy or any readily available English translations of pertinent portions of any non-English language references.
- A check or credit card payment form is attached in the amount required under 37 CFR §1.17(p).

RELATED CASES

- Attached is a list of applicant's pending application(s), published application(s) or issued patent(s) which may be related to the present application. In accordance with the waiver of 37 CFR 1.98 dated September 21, 2004, copies of the cited pending applications are not provided. Cited published and/or issued patents, if any, are listed on the attached PTO form 1449.
- A check or credit card payment form is attached in the amount required under 37 CFR §1.17(p).

CERTIFICATION

- Each item of information contained in this information disclosure statement was first cited in any communication from a foreign patent office in a counterpart foreign application not more than three months prior to the filing of this statement.
- No item of information contained in this information disclosure statement was cited in a communication from a foreign patent office in a counterpart foreign application or, to the knowledge of the undersigned, having made reasonable inquiry, was known to any individual designated in 37 CFR §1.56(c) more than three months prior to the filing of this statement.

DEPOSIT ACCOUNT

- Please charge any additional fees for the papers being filed herewith and for which no check or credit card payment is enclosed herewith, or credit any overpayment to deposit account number 15-0030. A duplicate copy of this sheet is enclosed.

Respectfully submitted,

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Form PTO 1449 (Modified)		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY DOCKET NO. 263098US2X PCT		SERIAL NO. New U.S. PCT Application Based on PCT/FR03/02225	
LIST OF REFERENCES CITED BY APPLICANT		APPLICANT Lea DI CIOCCIO, et al.					
		FILING DATE Herewith		GROUP			
U.S. PATENT DOCUMENTS							
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
AA		6 150 239	11/21/00	TONG, Qin-Yi et al.			
AB							
AC							
AD							
AE							
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AG							
AH							
AI							
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AK							
AL							
AM							
AN							
FOREIGN PATENT DOCUMENTS							
		DOCUMENT NUMBER	DATE	COUNTRY	TRANSLATION		
AO		02 37556	05/10/02	WO(with English abstract)	YES	NO	
AP							
AQ							
AR							
AS							
AT							
AU							
OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, etc.)							
AV	HUGONNARD-BRUYERE E ET AL: "Electrical and physical behavior of SiC layers on insulator (SiCOI)" INTERNATIONAL CONFERENCE ON SILICON CARBIDE AND RELATED MATERIALS, ICSRM'99, vol. 338-342, pt. 1, pages 715-718, October 1999.						
AW	HUGONNARD-BRUYERE E ET AL: "Defect Studies in Epitaxial SiC-6H layers on Insulator (SiCOI)" MICROELECTRONIC ENGINEERING, vol. 48, no. 1-4, pages 277-280, September 1999.						
AX	HUGONNARD-BRUYERE E ET AL: "Deep level defects in Himplanted 6H-SiC epilayers and in silicon carbide on insulator structures" MATERIAL SCIENCE AND ENGINEERING B, vol. 61-62, pages 382-388, July 30, 1999.						
AY	GREGORY R B ET AL: "The effects of damage on hydrogen-implant-induce thin-film seperation from bulk silicon carbide" WIDE-BANDGAP SEMICONDUCTORS FOR HIGH-POWER, HIGH-FREQUENCY AND HIGH-TEMPERATURE APPLICATIONS-1999. SYMPOSIUM, WIDE-BANDGAP SEMICONDUCTORS FOR HIGH-POWER, HIGH-FREQUENCY AND HIGH-TEMPERATURE APPLICATIONS -1999. vol. 572, pages 33-38, 1999.						
AZ	BINARI S C ET AL: "H, He, and N implant isolation of n-type GaN" JOURNAL OF APPLIED PHYSICS. vol.78, no. 5, September 1, 1995.				<input type="checkbox"/> Additional References sheet(s) attached		
Examiner					Date Considered		
*Examiner: Initial if reference is considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.							